PCN Number		2023121	.9007.1	PCN Da	ate:	D	ecember 22, 2023
Title: Qu	alification o	of DFAB as	s an addition	al Fab Site optic	on for seled	ct devic	es
Customer Co	ntact:	Cha	ange Manage	ment team	Dept:	Qu	uality Services
Proposed 1 st	Ship Date:	Ма	r 20, 2024		ted Sam	בו ו	n 20, 2024*
-				0, 2024 will no	Availabili ot be sup	ty:	-
Change Type			i January 2	0, 2024 Will In	n ne sup	porteu.	
Assembly S			Design			Vafer Bi	Imp Material
Assembly I			Data Sheet				Imp Process
Assembly I			Part numbe	r change		Vafer Fa	· · · ·
	Specificatio		Test Site		M N	Vafer Fa	b Materials
Packing/Sh	ipping/Labe	ling	Test Proces	S	N	Vafer Fa	ib Process
			DON				
Description of	fChanger		PCN	Details			
-		sed to an	nounce the c	ualification of D	FAB 200m	ım as aı	n additional wafer
				duct affected s	ection.		
	Current Fa	ab Site			Additiona	I Fab S	ite
Current Fal	Proce	ess	Wafer	Additional	Proc	ess	Wafer
Site SFAB	CD40	0.0	Diameter	Fab Site DFAB	CD4	000	Diameter
SFAD	CD40	00	150 mm	DFAD	CD40	000	200 mm
Qual details ar	e provided i	in the Qua	al Data Secti	on.			
Reason for C							
These changes	are part of	our mult	ivear plan to	transition produ	icts from (our 150	- millimotor
		efficient n	nanufacturing	processes and			
commitment t	product lo	efficient n ngevity a	nanufacturing nd supply co	processes and ntinuity.	technolog	ies, und	lerscoring our
commitment t Anticipated i	product lo	efficient n ngevity a	nanufacturing nd supply co	processes and	technolog	ies, und	lerscoring our
commitment t Anticipated i None	product lo mpact on F	efficient n ngevity a orm, Fit ,	nanufacturing nd supply co , Function, (processes and ntinuity. Quality or Relia	technolog ability (po	ies, und	lerscoring our
commitment t Anticipated i None	product lo mpact on F	efficient n ngevity a orm, Fit ,	nanufacturing nd supply co , Function, (processes and ntinuity.	technolog ability (po	ies, und	lerscoring our
commitment t Anticipated i None	product lo mpact on F	efficient n ngevity a orm, Fit ,	nanufacturing nd supply co , Function, (processes and ntinuity. Quality or Relia	technolog ability (po	ies, und	lerscoring our
commitment t Anticipated i None Changes to p Fab Site Inf	product lo mpact on F roduct ide prmation:	efficient n ngevity a orm, Fit, ntificatio	nanufacturing nd supply co , Function, (on resulting Site Origin	processes and ntinuity. Quality or Relia from this PCN Chip Site	technolog ability (po : Country	ies, und	lerscoring our / negative):
commitment t Anticipated i None Changes to p Fab Site Info Chip S	product lo mpact on F roduct ider prmation:	efficient n ngevity a orm, Fit, ntificatio	nanufacturing nd supply co , Function, (on resulting Site Origin de (20L)	processes and ntinuity. Quality or Relia from this PCN Chip Site Code (technolog ability (po : Country (21L)	ies, und	lerscoring our / negative): Chip Site City
commit ment t Anticipated i None Changes to p Fab Site Inf Chip S SH-BI	product lo mpact on F roduct ide prmation: Site	efficient n ngevity a orm, Fit, ntificatio	Site Origin de (20L)	from this PCN Chip Site Code (technolog ability (po : Country (21L) A	ies, und	lerscoring our / negative): Chip Site City Sherman
commitment t Anticipated i None Changes to p Fab Site Info Chip S	product lo mpact on F roduct ide prmation: Site	efficient n ngevity a orm, Fit, ntificatio	nanufacturing nd supply co , Function, (on resulting Site Origin de (20L)	processes and ntinuity. Quality or Relia from this PCN Chip Site Code (technolog ability (po : Country (21L) A	ies, und	lerscoring our / negative): Chip Site City
commit ment t Anticipated i None Changes to p Fab Site Inf Chip S SH-BI	product lo mpact on F roduct ider prmation: Site P-1 IN	cficient n ngevity a orm, Fit, ntificatio	nanufacturing nd supply co , Function, (on resulting Site Origin de (20L) SHE DLN	processes and ntinuity. Quality or Relia from this PCN Chip Site Code (US	technolog ability (po : Country (21L) A	ies, und	lerscoring our / negative): Chip Site City Sherman
commitment t Anticipated i None Changes to p Fab Site Inf Chip S SH-BI DL-1 Sample product MADE IN: Malay 2DC: 2/260C/1 MSL 2 /260C/1 MSL 2 /260C/1 MSL 2 /260C/1 MSL 2 /260C/1	product lo mpact on F roduct ider prmation: Site P-1 IN et shipping I Sia YEAR SEAL DT LIM 03/29/04 .)TO:1750	abel (not	Site Origin de (20L) SHE DLN actual produ	ct label) P) SN74LS07NS Quality or Relia from this PCN Chip Site Code (US US Ct label) P) SN74LS07NS Q) 2000 (D TT) LOT: 39590 W) TKY (1T) 752 P) REV: (Y) D) CSP: SHE (21L	technolog a bility (per : Country (21L) A A A R) 0336 47MLA	ies, und	lerscoring our / negative): Chip Site City Sherman
commitment t Anticipated i None Changes to p Fab Site Inf Chip S SH-BI DL-L Sample product Sample product MADE IN: Malay 2DC: 20 MSL '2 /260C/1 MSL 1 /235C/UM OPT: ITEM:	product lo mpact on F roduct ider prmation: Site P-1 IN et shipping I Sia YEAR SEAL DT LIM 03/29/04 .)TO:1750	abel (not	Site Origin de (20L) SHE DLN actual produ	ct label) P) SN74LS07NS Quality or Relia from this PCN Chip Site Code (US US Ct label) P) SN74LS07NS Q) 2000 (D TT) LOT: 39590 W) TKY (1T) 752 P) REV: (Y) D) CSP: SHE (21L	technolog a bility (po country (21L) A A A A A A 0336 47MLA 23483S12 0033317 00033317	ies, und	lerscoring our / negative): Chip Site City Sherman
commitment t Anticipated i None Changes to p Fab Site Inf Chip S SH-BI DL-1 Sample product MADE IN: Malay 2DC: 2/260C/1 MSL 2 /260C/1 MSL 2 /260C/1 MSL 2 /260C/1 MSL 2 /260C/1	product lo mpact on F roduct ide prmation: Site P-1 IN t shipping I Sia YEAR SEAL DT LIM 03/29/04 39 .)TO: 1750 Sted:	abel (not	An ufacturing nd supply co , Function, (on resulting Site Origin de (20L) SHE DLN actual produ	ct label) P) SN74LS07NS Quality or Relia from this PCN Chip Site Code (US US Ct label) P) SN74LS07NS Q) 2000 (D TT) LOT: 39590 W) TKY (1T) 752 P) REV: (Y) D) CSP: SHE (21L	technolog ability (po country (21L) A A A A B 0336 47MLA 23483S12 0033317 cco-usa) Aco: Mys	ies, und	lerscoring our / negative): Chip Site City Sherman
commitment t Anticipated i None Changes to p Fab Site Inf Chip S SH-BI DL-L Sample product MaDE IN: Malay 2DC: 20 MSL '2 /260C/1 MSL '2 /260C/1	product lo mpact on F roduct ider prmation: Site P-1 IN tt shipping I Sia YEAR SEAL DT LIM 03/29/04 .)TO:1750 cted:	abel (not	Site Origin de (20L) SHE DLN actual produ	processes and ntinuity. Quality or Relia from this PCN Chip Site Code (US US ct label) P) SN74LS07NS Q) 2000 (D IT) LOT: 39590 W) TKY (1T) 752 D) REV: (V) D) CSO: SHE (21L 21) ASO: MLA (22L	technolog ability (po country (21L) A A A A B 0336 47MLA 23483S12 0033317 cco-usa) Aco: Mys	c CD40	lerscoring our / negative): Chip Site City Sherman Dallas

CD14538BPWR	CD4030BE	CD4050BEE4	CD4094BE
CD14538BPWRG4	CD4030BEE4	CD4050BNSR	CD4094BEE4
CD4001BE	CD4030BM96	CD4050BPWR	CD4094BNSR
CD4001BEE4	CD4030BM96G4	CD4056BM96	CD4094BPWR
CD4001BM	CD4042BDR	CD4069UBE	CD4098BE
CD4001BM96	CD4042BDRG4	CD4069UBEE4	CD4098BEE4
CD4001BM96E4	CD4042BE	CD4069UBM	CD4098BM96
CD4001BM96G4	CD4042BEE4	CD4069UBM96	CD4098BM96G4
CD4001BPWR	CD4043BDR	CD4069UBNSR	CD4511BE
CD40107BE	CD4043BDRG4	CD4069UBPWR	CD4511BEE4
CD40107BM	CD4043BDWR	CD4070BE	CD4511BNSR
CD40107BM96	CD4043BE	CD4070BEE4	CD4511BNSRG4
CD4011BE	CD4043BEE4	CD4070BM96	CD4511BPWR
CD4011BEE4	CD4043BPWR	CD4070BM96E4	CD4512BE
CD4011BM	CD4044BDR	CD4070BPWR	CD4512BEE4
CD4011BM96	CD4044BE	CD4071BE	CD4512BM96
CD4011BM96E4	CD4044BEE4	CD4071BEE4	CD4512BM96G4
CD4011BME4	CD4044BNSR	CD4071BM96	CD4514BM96
CD4011BNSR	CD4044BPWR	CD4072BE	CD4515BM96
CD4011BPWR	CD4046BE	CD4072BM96	CD4517BE
CD4011BPWRG4	CD4046BEE4	CD4072BM96G4	CD4520BE
CD4014BE	CD4046BNSR	CD4072BNSR	CD4520BEE4
CD4014BM96	CD4046BNSRE4	CD4073BE	CD4520BM96
CD4021BE	CD4047BE	CD4073BEE4	CD4536BE
CD4021BEE4	CD4047BEE4	CD4073BM96	CD4536BEE4
CD4021BM96	CD4047BM96	CD4077BE	CD4536BNSR
CD4021BM96E4	CD4047BM96G4	CD4078BM96	CD4543BE
CD4021BPWR	CD4047BPWR	CD4078BPWR	CD4543BEE4
CD4023BE	CD4049UBDR	CD4078BPWRE4	CD4543BM96
CD4023BEE4	CD4049UBDRE4	CD4081BE	CD4555BM96
CD4023BM96	CD4049UBDRG4	CD4081BEE4	CD4555BPWR
CD4023BNSR	CD4049UBE	CD4081BM	CD4555BPWRG4
CD4023BPWR	CD4049UBEE4	CD4081BM96	
CD4024BE	CD4049UBNSR	CD4081BM96G4	

For alternate parts with similar or improved performance, please visit the product page on $\underline{\text{TI.com}}$

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

PCA1A113AASTA2JEDEC JESCAC/UHASTA3JEDEC JESCAC/UHASTA3JEDEC JESCTCA4JEDEC JESCTC-BPA4MIL-STD883TC-SAMA4-HTSLA6JEDEC JESCTest Group B - Accelerated LifetingJEDEC JESCELFRB1JEDEC JESCSDC3JEDEC JESCSDC3JEDEC JESCEMD1JESD61	TD-020 JESD22- D22-A110 D22-A102/JEDEC 18 D22-A104 and 3 Method 2011 D22-A103 me Simulation Tests D22-A108 D22-A108 D22-A108 D22-A108 D22-A108	3 3 3 3 1 3 1 1	77 77 77 5 3 45 77 800	Preconditioning Biased HAST Unbiased HAST Temperature Cycle Post Temp Cycle Bond Pull Post TC SAM High Temperature Storage Life Early Life Failure Rate	MSL1 260C 130C/85%RH 130C/85%RH -65C/150C - <50% delamination 150C 125C 125C	- 96 Hours 96 Hours 500 Cycles - - 1000 Hours 1000 Hours 48 Hours	3/0/0 3/231/0 3/231/0 3/231/0 1/5/0 3/36/0 1/45/0 3/231/0 3/2400/0
FC A1 A113 HAST A2 JEDEC JESI AC/UHAST A3 JEDEC JESI AC/UHAST A3 JEDEC JESI AC/UHAST A3 JEDEC JESI TC A4 JEDEC JESI TC-BP A4 MIL-STD883 TC-SAM A4 - HTSL A6 JEDEC JESI Test Group B - Acceutated Lifetin HTOL B1 JEDEC JESI ELFR B2 AEC Q100-0 Test Group C - Package Assembly SD C3 JEDEC J-ST SD C3 JEDEC J-ST SD C3 JEDEC J-ST Test Group D - Die Fabrication Re EM D1 JESD61 Type # Test TDDB D2 JESD35	D22-A110 D22-A102/JEDEC 18 D22-A104 and 3 Method 2011 D22-A103 me Simulation Tests D22-A108 D22-A108 D22-A108 D22-A108	3 3 3 1 3 1 3 3 3	777 777 5 3 45 777	Biased HAST Unbiased HAST Temperature Cycle Post Temp Cycle Bond Pull Post TC SAM High Temperature Storage Life Test	130C/85%RH 130C/85%RH -65C/150C - <50% delamination 150C 125C	96 Hours 96 Hours 500 Cycles - - 1000 Hours 1000 Hours 48	3/231/0 3/231/0 3/231/0 1/5/0 3/36/0 1/45/0 3/231/0
AC/UHASTA3JEDEC JEST JESD22-A11TCA4JEDEC JEST JESD22-A11TC-BPA4MIL-STD883TC-SAMA4-HTSLA6JEDEC JESTTest Group B - Accettated LifetingJEDEC JESTHTOLB1JEDEC JESTELFRB2AEC Q100-0Test Group C - Package AssemblySDC3SDC3JEDEC J-STSDC3JEDEC J-STTest Group D - Die E-brication ReEMEMD1JESD61Type#TeTDDBD2JESD35	D22-A102/JEDEC 18 D22-A104 and 3 Method 2011 D22-A103 me Simulation Tests D22-A108 D22-A108 008 y Integrity Tests	3 3 1 3 1 3 3 3	77 77 5 3 45 77	Unbiased HAST Temperature Cycle Post Temp Cycle Bond Pull Post TC SAM High Temperature Storage Life Test	130C/85%RH -65C/150C - <50% delamination 150C 125C	Hours 96 Hours 500 Cycles - - 1000 Hours 1000 Hours 48	3/231/0 3/231/0 1/5/0 3/36/0 1/45/0 3/231/0
ACIOHAST A3 JESD22-A11 TC A4 JEDEC JEST Appendix 3 TC-BP A4 MIL-STD883 TC-SAM A4 - HTSL A6 JEDEC JEST Test Group B - Accettated Lifetin HTOL B1 JEDEC JEST ELFR B2 AEC Q100-0 Test Group C - Package Assembly SD C3 JEDEC J-ST SD C3 JEDEC J-ST Test Group D - Die Fabrication Re EM D1 JESD61 Type # Test	18 D22-A104 and 3 Method 2011 D22-A103 me Simulation Tests D22-A108 008 y Integrity Tests	3 1 3 1 3 3 3	77 5 3 45 77	Temperature Cycle Post Temp Cycle Bond Pull Post TC SAM High Temperature Storage Life	-65C/150C - <50% delamination 150C 125C	Hours 500 Cycles - - 1000 Hours 1000 Hours 48	3/231/0 1/5/0 3/36/0 1/45/0 3/231/0
IC A4 Appendix 3 TC-BP A4 MIL-STD883 TC-SAM A4 - HTSL A6 JEDEC JESE Test Group B - Accetrated Lifetin HTOL B1 JEDEC JESE ELFR B2 AEC Q100-0 Test Group C - Package Assembly SD C3 JEDEC J-ST SD C3 JEDEC J-ST Test Group D - Die Fabrication Re EM D1 JESD61 Type # Te TDDB D2 JESD35	3 Method 2011 D22-A103 me Simulation Tests D22-A108 008 y Integrity Tests	1 3 1 3 3	5 3 45 77	Post Temp Cycle Bond Pull Post TC SAM High Temperature Storage Life	- <50% delamination 150C 125C	Cycles - - 1000 Hours 1000 Hours 48	1/5/0 3/36/0 1/45/0 3/231/0
TC-SAM A4 - HTSL A6 JEDEC JESC Test Group B - Accettad Lifetin HTOL B1 JEDEC JESC ELFR B2 AEC Q100-0 Test Group C - Package Assembly SD C3 JEDEC J-ST Tots Group D - Die Fabrication Re EM D1 JESD61 Type # Test D35 TDDB D2 JESD35	D22-A103 me Simulation Tests D22-A108 008 y Integrity Tests	3 1 3 3 3	3 45 77	Pull Post TC SAM High Temperature Storage Life Life Test	<50% delamination 150C 125C	- 1000 Hours 1000 Hours 48	3/36/0 1/45/0 3/231/0
HTSL A6 JEDEC JESC Test Group B - Accelerated Lifetin HTOL B1 JEDEC JESC ELFR B2 AEC Q100-0 Test Group C - Package Assembly SD C3 JEDEC J-ST SD C3 JEDEC J-ST Test Group D - Die Fabrication Re EM D1 JESD61 Type # Te	me Simulation Tests D22-A108)08 y Integrity Tests	1 3 3	45 77	High Temperature Storage Life	150C 125C	1000 Hours 1000 Hours 48	1/45/0 3/231/0
Test Group B - Accelerated Lifetin HTOL B1 JEDEC JEST ELFR B2 AEC Q100-0 Test Group C - Package Assembly SD C3 JEDEC J-ST SD C3 JEDEC J-ST SD C3 JEDEC J-ST Test Group D - Die Fabrication Re EM D1 JESD61 Type # Te TDDB D2 JESD35	me Simulation Tests D22-A108)08 y Integrity Tests	3	77	Life Test	125C	Hours 1000 Hours 48	3/231/0
HTOL B1 JEDEC JESE ELFR B2 AEC Q100-0 Test Group C - Package Assembly SD C3 JEDEC J-ST SD C3 JEDEC J-ST Test Group D - Die Fabrication Re EM D1 JESD61 Type # Te	D22-A108 008 Iy Integrity Tests	3				Hours 48	
ELFR B2 AEC Q100-0 Test Group C - Package Assembly SD C3 JEDEC J-ST SD C3 JEDEC J-ST Test Group D - Die Fabrication Re EM D1 JESD61 Type # Te	008 ly Integrity Tests	3				Hours 48	
Test Group C - Package Assembly SD C3 JEDEC J-STI SD C3 JEDEC J-STI SD C3 JEDEC J-STI Test Group D - Die Fabrication Re EM D1 JESD61 Type # Te TDDB D2 JESD35	ly Integrity Tests		800	Early Life Failure Rate	125C		3/2400/0
SD C3 JEDEC J-ST SD C3 JEDEC J-ST Test Group D - Die Fabrication Re EM D1 JESD61 Type # Te TDDB D2 JESD35		1					
SD C3 JEDEC J-ST Test Group D - Die Fabrication Re EM D1 JESD61 Type # Ta TDDB D2 JESD35	D-002	1					
Test Group D - Die Fabrication Re EM D1 JESD61 Type # Te TDDB D2 JESD35			15	PB Solderability	>95% Lead Coverage	-	1/15/0
EM D1 JESD61 Type # Te TDDB D2 JESD35	D-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	1/15/0
Type # Te	liability Tests						
TDDB D2 JESD35		-	-	Electromigration	-	-	Completed Per Process Technology Requirements
	est Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>MSA00300PWR</u>
HCI D3 JESD60 & 2		-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements
	8	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements
BTI D4 -		-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements
SM D5 -		-	-	Stress Migration	-	-	Completed Per Process Technology Requirements
Test Group E - Electrical Verificati	ion Tests						
ESD E2 AEC Q100-0	002	1	3	ESD HBM	-	2000 Volts	1/3/0
ESD E3 AEC Q100-0	011	1	3	ESD CDM	-	750 Volts	1/3/0
LU E4 AEC Q100-0		1	6	Latch-Up	Per AEC Q100-004	-	1/6/0
ED E5 AEC Q100-0	004		30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

• The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

- QBS: Qual By Similarity
- Qual Device MSA00300PWR is qualified at MSL1 260C
- Qual Device MSA00300PWR is qualified at MSL1 260C

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2203-040

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

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